

## Buried Photodiode with Floating P+ Surface of Serious Image Lag Problem

The parasitic capacitance coupling with the surrounding depletion region and the gate oxide.

Pinned Photodiode must have the adjacent heavily doped P+ Channel Stops Region or a metal contact as an option as shown in JPA 1975-127646, JPA1975- 127647 and JPA 1975-134985 invented by Yoshiaki Hagiwara in 1975. See also SSDM1978 paper by Hagiwara in 1978.

